Entry of this amendment prior to calculating the filing fee is respectfully requested.

Respectfully submitted,

Steven R. Biren, Reg. 26,533

Attorney

(914) 333-9630 April 6, 2001

APPENDIX

- 3. (Amended) A method as claimed in claim $1 \, \text{or} \, 2$, characterized in that the depth (h) of the trench is equal to maximally half the height (H1) of the larger isolation layer and maximally half the thickness (E) of the larger isolation layer.
- 4. (Amended) A method as claimed in <u>claim 1</u> any one of the preceding claims, characterized in that the vertical portion of the smaller isolation layer (402) is anisotropically etched.
- 5. (Amended) A method as claimed in <u>claim 1</u> any one of the elaims 1 to 3, characterized in that the vertical portion of the smaller isolation layer (402) is isotropically etched.
- 8. (Amended) An integrated circuit as claimed in claim 6 or 7, characterized in that the depth (h) of the trench (TR) is equal to maximally half the height (H1) of the larger isolation layer and equal to maximally half the thickness (E) of the larger isolation layer.
- 9. (Amended) An integrated circuit as claimed in <u>claim 6</u> any one of the claims 6 to 8, characterized in that each lateral isolation region comprises a horizontal trench (TH) made in the smaller isolation layer (402) between the larger isolation layer (411) and the substrate (1) of the integrated circuit, said trench extending from the lateral edge of the larger isolation layer of the lateral isolation region.